

MOSFETs Silicon N-channel MOS (U-MOSIX-H)

# TK4R3E06PL

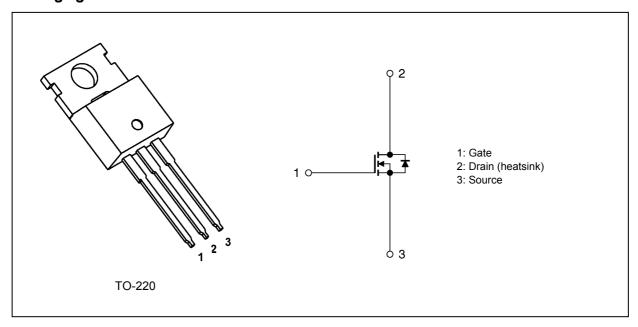
#### 1. Applications

- High-Efficiency DC-DC Converters
- Switching Voltage Regulators
- · Motor Drivers

#### 2. Features

- (1) High-speed switching
- (2) Small gate charge:  $Q_{SW} = 15.1 \text{ nC (typ.)}$
- (3) Small output charge:  $Q_{oss} = 39 \text{ nC (typ.)}$
- (4) Low drain-source on-resistance:  $R_{DS(ON)} = 3.3 \text{ m}\Omega$  (typ.) ( $V_{GS} = 10 \text{ V}$ )
- (5) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 60 \text{ V)}$
- (6) Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 0.5 mA)

#### 3. Packaging and Internal Circuit



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## 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	60	V
Gate-source voltage			$V_{GSS}$	±20	
Drain current (DC)	(T <sub>c</sub> = 25 °C)	(Note 1)	I <sub>D</sub>	80	Α
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	$I_D$	106	
Drain current (pulsed)	(t = 100 μs)	(Note 1)	I <sub>DP</sub>	350	
Power dissipation	$(T_c = 25 ^{\circ}C)$		$P_D$	87	W
Single-pulse avalanche energy		(Note 3)	E <sub>AS</sub>	29	mJ
Single-pulse avalanche current		(Note 3)	I <sub>AS</sub>	80	Α
Channel temperature			T <sub>ch</sub>	175	°C
Storage temperature			T <sub>stg</sub>	-55 to 175	°C
Mounting torque			TOR	0.6	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance $(T_c = 25  ^{\circ}\text{C})$	R <sub>th(ch-c)</sub>	1.72	°C/W
Channel-to-ambient thermal resistance (T <sub>a</sub> = 25 °C)	R <sub>th(ch-a)</sub>	83.3	

Note 1: Ensure that the channel temperature does not exceed 175 °C.

Note 2: Limited by silicon chip capability.

Note 3:  $V_{DD}$  = 48 V,  $T_{ch}$  = 25 °C (initial), L = 3.5  $\mu$ H,  $I_{AS}$  = 80 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

## 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±0.1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	_		10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	60			V
Drain-source breakdown voltage (Note 4)	V <sub>(BR)DSX</sub>	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	45	_		
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.5 mA	1.5	_	2.5	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 15 A	_	5.2	7.2	mΩ
		V <sub>GS</sub> = 10 V, I <sub>D</sub> = 34 A	_	3.3	4.3	

Note 4: If a reverse bias is applied between gate and source, this device enters  $V_{(BR)DSX}$  mode. Note that the drain-source breakdown voltage is lowered in this mode.

## 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	3280	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	60	_	
Output capacitance	C <sub>oss</sub>		_	600	_	
Gate resistance	r <sub>g</sub>	_	_	1.7	_	Ω
Switching time (rise time)	t <sub>r</sub>	See Fig. 6.2.1	_	10	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	24	_	
Switching time (fall time)	t <sub>f</sub>		_	18	_	
Switching time (turn-off time)	t <sub>off</sub>		_	55	_	

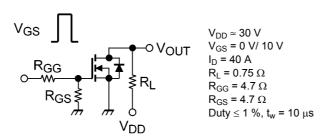


Fig. 6.2.1 Switching Time Test Circuit

## 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	$Q_g$	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$	-	48.2		nC
gate-drain)		$V_{DD} \approx 30 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 40 \text{ A}$		23.9		
Gate-source charge 1	Q <sub>gs1</sub>	$V_{DD} \approx 30 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 40 \text{ A}$		13.1		
Gate-drain charge	$Q_{gd}$		_	8.6	_	
Gate switch charge	$Q_{SW}$		_	15.1	_	
Output charge	$Q_{oss}$	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	_	39	_	



## 6.4. Source-Drain Characteristics ( $T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed) (Note 5)	I <sub>DRP</sub> (t = 100 μs)	_	1	I	350	Α
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 80 A, V <sub>GS</sub> = 0 V			-1.5	V
Reverse recovery time	t <sub>rr</sub>	$I_{DR}$ = 20 A, $V_{GS}$ = 0 V,		47	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs		57	_	nC

Note 5: Ensure that the channel temperature does not exceed 175 °C.

## 7. Marking

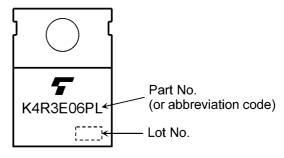


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)

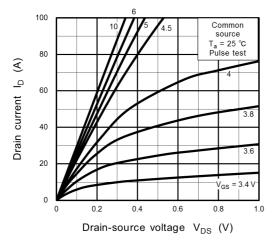


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

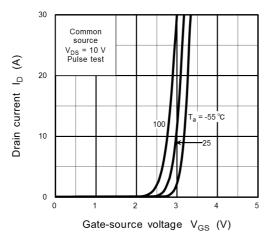


Fig. 8.3  $I_D - V_{GS}$ 

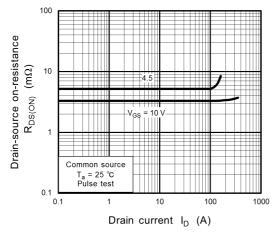


Fig. 8.5 R<sub>DS(ON)</sub> - I<sub>D</sub>

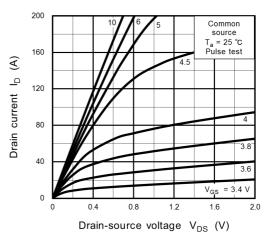


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

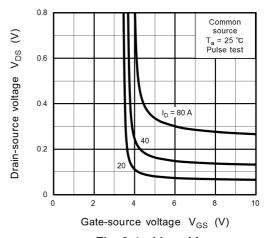


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

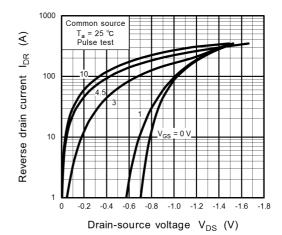


Fig. 8.6 IDR - VDS

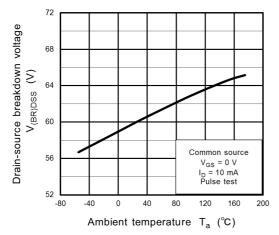


Fig. 8.7 V<sub>(BR)DSS</sub> - T<sub>a</sub>

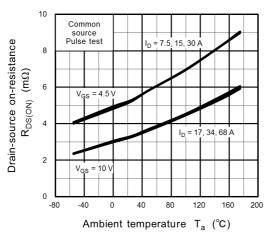


Fig. 8.9 R<sub>DS(ON)</sub> - T<sub>a</sub>

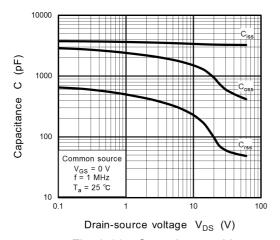


Fig. 8.11 Capacitance - V<sub>DS</sub>

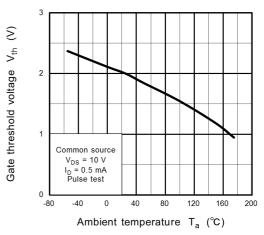


Fig. 8.8 V<sub>th</sub> - T<sub>a</sub>

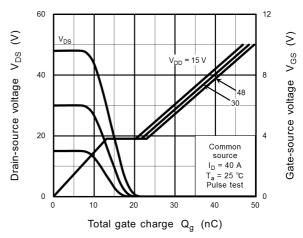


Fig. 8.10 Dynamic Input/Output Characteristics

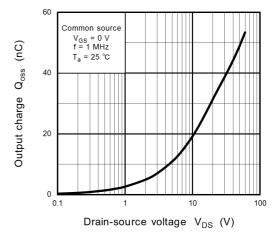


Fig. 8.12 Qoss - VDS

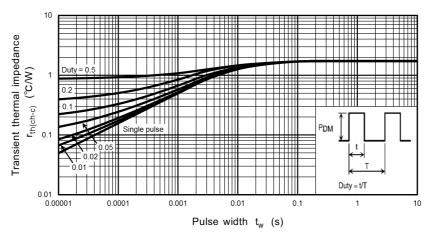
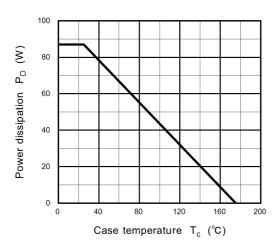


Fig. 8.13 r<sub>th</sub> - t<sub>w</sub> (Guaranteed Maximum)



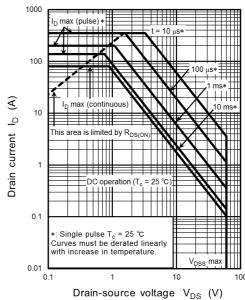


Fig. 8.14 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

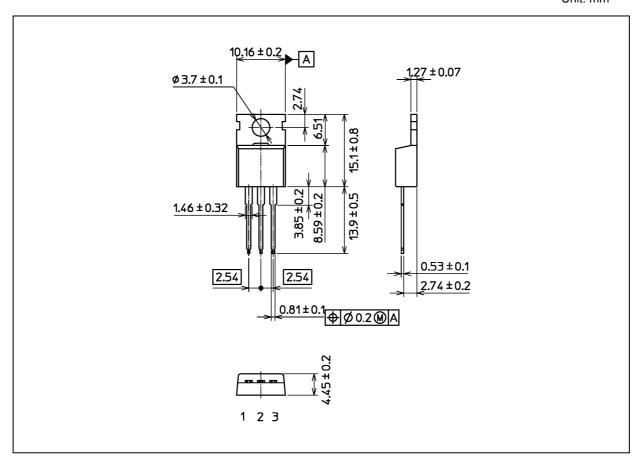
Fig. 8.15 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



## **Package Dimensions**

Unit: mm



Weight: 1.93 g (typ.)

	Package Name(s)
TOSHIBA: 2-10X1A	
Nickname: TO-220	



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